

- ☞ L34: (62) 33 and (channel adj region)
- ☞ L35: (57) 34 and (control adj gate floating adj gate)
- ☞ L37: (8) 36 and 'EEPROM'
- ☞ L38: (100) 31 and 26
- ☞ L39: (73) 38 and 29
- ☞ L40: (96) 38 and (implantation implanting implant\$2)
- ☞ L41: (95) 40 and (mask\$3 resist photo-resist phot adj resist resist)
- ☞ L42: (95) 41 and (source drain s/d source/drain drain)
- ☞ L52: (1440) lightly adj3 source
- ☞ L53: (1126) 52 and (mask\$3 resist photo-resist phot adj resist resist)
- ☞ L54: (1067) 53 and (implantation implanting implant\$2)
- ☞ L55: (1067) 54 and (source drain s/d source/drain drain)
- ☞ L56: (178) 55 and (control adj gate floating adj gate)
- ☞ L57: (1064) 55 and (gate)
- ☞ L58: (479) 57 and (flash memory)
- ☞ L59: (236) 58 and (channel adj region)
- ☞ L60: (133) 56 and (channel adj region)
- ☞ L61: (163) 56 and (channel)
- ☞ L36: (283) ((lightly adj3 source) with (mask\$3 resist photo adj resist photoresist) same (imp...)
- ☞ L63: (1) "5866453".PN.

Search List Browse Queue Clear

DBs: USPAT: US-PGPUB; EPO; JPO; DE ☐ Plurals

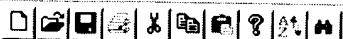
Default operator: OR

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((lightly adj3 source) with (mask\$3 resist photo adj resist photoresist) same (implanting implant\$2))

BRS form IS&R form Image Text HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20020048862 A1	20020425	10	Fully self-aligned fet technology	438/151	438/163; 438/305
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020045320 A1	20020418	11	Nonvolatile memory device and method for manufacturing the same	438/303	365/185.15; 438/257
3			US 20020022375 A1	20020221	12	METHOD OF MAKING ULTRA	438/287	438/501



- ☞ L26: (35847) 'EEPROM'
- ☞ L27: (30041) 26 and memory
- ☞ L28: (11389) 27 and flash
- ☞ L29: (1919) 28 and (implantation implanting implant\$2)
- ☞ L30: (1519) 29 and (mask\$3 resist photo-resist phot adj resist resist)
- ☞ L31: (1440) lightly adj3 source
- ☞ L32: (77) 30 and 31
- ☞ L33: (77) 32 and (source drain s/d source/drain drain)
- ☞ L34: (62) 33 and (channel adj region)
- ☞ L35: (57) 34 and (control adj gate floating adj gate)
- ☞ L36: (283) ((lightly adj3 source) with (mask\$3 resist photo adj resist ph
- ☞ L37: (8) 36 and 'EEPROM'
- ☞ L38: (100) 31 and 26
- ☞ L39: (73) 38 and 29
- ☞ L40: (96) 38 and (implantation implanting implant\$2)
- ☞ L41: (95) 40 and (mask\$3 resist photo-resist phot adj resist resist)
- ☞ L42: (95) 41 and (source drain s/d source/drain drain)

Failed

DBs: USPAT; US-PGPUB; EPO; JPO; DEF ☐ Plurals

Default operator: OR

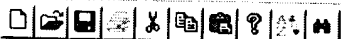
☒ Highlight all hit terms initially

41 and (source drain s/d source/drain drain)

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6359305 B1	20020319	21	Trench-isolated EEPROM flash in segmented bit line page architecture	257/316	257/321;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6356486 B1	20020312	40	Electrically alterable non-volatile memory with n-bits per cell	365/189.01	438/267 365/185.1;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6353554 B1	20020305	57	Memory apparatus including	365/185.03	365/185.2; 365/230.01

Ready

NUM



- ✓ L26: (35847) 'EEPROM'
- ✓ L27: (30041) 26 and memory
- ✓ L28: (11389) 27 and flash
- ✓ L29: (1919) 28 and (implantation implanting implant\$2)
- ✓ L30: (1519) 29 and (mask\$3 resist photo-resist phot adj resist resist)
- ✓ L31: (1440) lightly adj3 source
- ✓ L32: (77) 30 and 31
- ✓ L33: (77) 32 and (source drain s/d source/drain drain)
- ✓ L34: (62) 33 and (channel adj region)
- ✓ L35: (57) 34 and (control adj gate floating adj gate)

Failed

Search

DBs: USPAT: US-PGPUB: EPO: JPO: DE ☐ Plurals

Default operator: OR

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34 and (control adj gate floating adj gate)

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6359305 B1	20020319	21	Trench-isolated EEPROM flash in segmented bit line page architecture	257/316	257/321;
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6356486 B1	20020312		Electrically alterable non-volatile memory with n-bits per cell	365/189.01	438/267
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6353554 B1	20020305		Memory apparatus including programmable non-volatile multi-bit	365/185.03	365/185.1;
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6344998 B1	20020205		Electrically alterable non-volatile memory with N-Bits per cell	365/185.22	365/185.2;
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6343034 B1	20020129		Electrically alterable non-volatile memory with n-bits per cell	365/189.01	365/230.01
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6339545 B1	20020115		Electrically alterable non-volatile memory with n-bits per cell	365/185.03	365/230.02
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6335549 B1	20020101		EEPROM with high channel hot carrier injection efficiency	257/231	365/201;
								365/207
								257/315;
								257/231;

Ready

NUM



Drafts

Pending

Active

- L1: (7326) (memory same flash) and 'EEPROM'
- L2: (1691) 1 and (implantation implanting implant\$2)
- L3: (1662) 2 and (source drain s/d source/drain)
- L4: (1348) 3 and mask\$3
- L5: (1335) 4 and gate
- L6: (107) 5 and (lightly near3 source)
- L7: (966) 5 and (channel near3 region)
- L8: (91) 7 and (lightly near3 source)

BRIEF

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DBs

USPAT; US-PGPUB; EPD; JPO; DERWENT; IBM_TDB

☒ Plurals

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Type	Hits	Search Text	DBs	Time Stamp	Comments

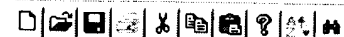
Hits

Details

HTML

Ready

NUM



Pending

Active

- L1: (7326) (memory same flash) and 'EEPROM'
- L2: (1691) 1 and (implantation implanting implant\$2)
- L3: (1662) 2 and (source drain s/d source/drain)
- L4: (1348) 3 and mask\$3
- L5: (1335) 4 and gate
- L6: (107) 5 and (lightly near3 source)
- L7: (966) 5 and (channel near3 region)
- L8: (91) 7 and (lightly near3 source)
- L17: (21019) 'EEPROM'
- L18: (37762) 'EEPROM'
- L19: (10777) (memory same flash) and 'EEPROM'
- L21: (7392) 19 and (source s/d drain source/drain)
- L24: (4059) 21 and (control adj gate floating adj gate)
- L25: (1835) 24 and (mask\$3 resist photo and resist resist)

Failed

Saved

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DBs USPAT: US-PGPUB: EPO: JPO: DE ☒ Plurals

Default operator: OR

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24 and (mask\$3 resist photo and resist resist)

BRS form

IS&R form

Image

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U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R

Hits

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